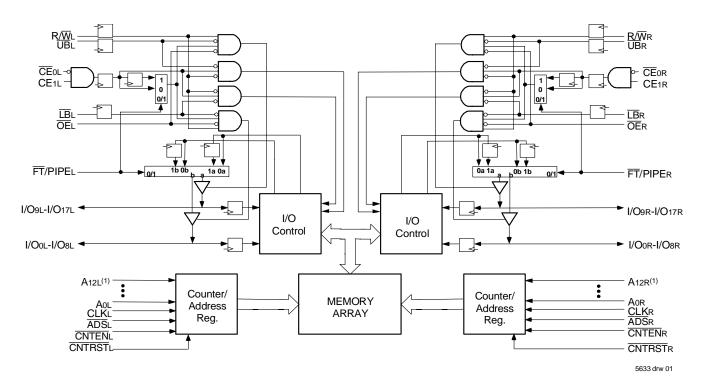
HIGH-SPEED 8/4K x 18 SYNCHRONOUS PIPELINED **DUAL-PORT STATIC RAM**

Features

Features	1
 True Dual-Ported memory cells which allow simultaneous 	Full synchronous operation on both ports
access of the same memory location	- 3.5ns setup to clock and Ons hold on all control, data, and
 High-speed clock to data access 	address inputs
– Commercial: 6.5/7.5/9ns (max.)	 Data input, address, and control registers
– Industrial: 7.5ns (max.)	- Fast 6.5ns clock to data out in the Pipelined output mode
 Low-power operation 	 Self-timed write allows fast cycle time
– IDT709359/49L	– 10ns cycle time, 100MHz operation in Pipelined output mode
Active: 925mW (typ.)	Separate upper-byte and lower-byte controls for
Standby: 2.5mW (typ.)	multiplexed bus and bus matching compatibility
 Flow-Through or Pipelined output mode on either Port via 	 TTL- compatible, single 5V (±10%) power supply
the FT/PIPE pins	 Industrial temperature range (-40°C to +85°C) is
 Counter enable and reset features 	available for 83 MHz
 Dual chip enables allow for depth expansion without 	• Available in a 100-pin Thin Quad Flatpack (TQFP) package
additional logic	and a 100-pin fine pitch Ball Grid Array (fpBGA)

Functional Block Diagram



NOTE:

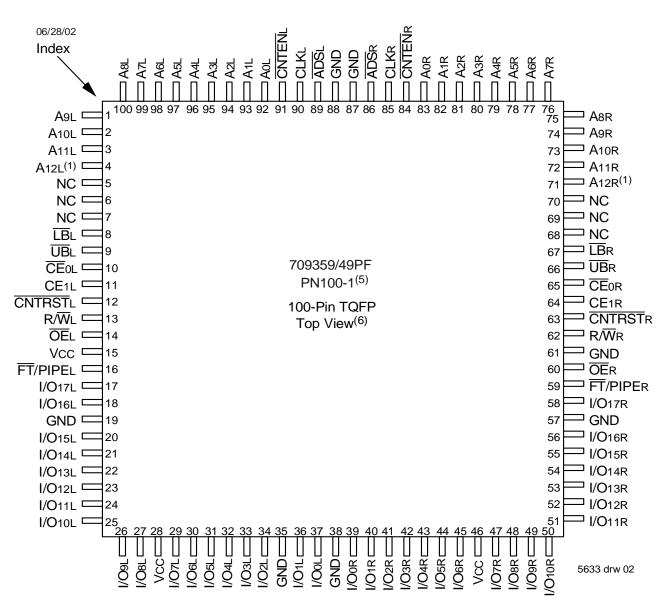
1. A12 is a NC for IDT709349.

DSC-5633/3

High-Speed 8/4K x 18 Synchronous Pipelined Dual-Port Static RAM

Description

The IDT709359/49 is a high-speed 8/4K x 18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT709359/49 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by $\overline{CE}o$ and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 925mW of power.



Pin Configurations^(1,2,3,4)

- 1. A12 is a NC for IDT709349.
- 2. All Vcc pins must be connected to power supply.
- 3. All GND pins must be connected to ground.
- 4. Package body is approximately 14mm x 14mm x 1.4mm
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Configurations (con't.)^(1,2,3,4)

06/28/02

709359/49BF BF100⁽⁵⁾

100-Pin fpBGA Top View⁽⁶⁾

00/20/02			_						
a1	a2	<u>.</u>	Α4	^{A5}	^{A6}	^{A7}	a8	a9	a10
A8r	A11r		CNTRSTR	GND	GND	GND	I/O13R	I/O10r	I/O17R
B1	^{B2}	b3	B4	^{b5}	-	³⁷	b8	b9	b10
A6R	A7R	A10r	A12R ⁽¹⁾	R/Wr		PL/FTr	I/O12R	I/O9r	I/O6R
C1	C2	C3	C4	C5	C6	C7	C8	C9	С10
A3R	A4R	A5R	A9R	CE1R	I/O16R	I/O15R	I/O11R	I/O7R	І/Озк
D1	d2	D3	D4	D5	D6	d7	d8	D9	D10
Aor	CLKr	A1R	A2R	LBR	CEOR	I/O14r	I/O8r	I/O5R	I/O1R
^{E1}	e2	E3	E4	e5	^{E6}	e7	e8	e9	E10
GND	ADSr	CNTEN _R	A1L	ADSl	GND	I/O4r	I/O2r	I/Oor	VCC
^{F1}	F2	F3	F4	F5	^{F6}	F7	F8	F9	f10
GND	CLKL	Aol	A3L	VCC	GND	Vcc	I/O2L	I/O1L	I/Ool
G1	G2	G3	G4	^{G5}	G6	^{G7} NC	G8	^{G9}	G10
CNTEN∟	A4L	A7L	UBL	GND	I/O13L		I/O4L	GND	I∕O3L
H1 A2L	H2 A6L	H3 A11L		H5 CNTRST∟		H7 I/O9∟	h8 I/O7l	H9 I/O6L	H10 I/O5L
J1	J2	J3	J4	J5	^{J6}	J7	j8	^{J9}	J10
A5L	A9L	A12L ⁽¹⁾	R∕₩L	OEL	PL∕ FT ∟	. I/O 12L	I/O10L	GND	I/O8L
K1	K2	K3	K4	K5	K6	к7	к8	к9	к10
A8L	A10L	LBL	CE1L	Vcc	Vcc	I/O16L	I/O14L	I/O11L	I/O17L

5633 drw 03

- 1. A12 is a NC for IDT709349.
- 2. All Vcc pins must be connected to power supply.
- 3. All GND pins must be connected to ground.
- 4. Package body is approximately 14mm x 14mm x 1.4mm
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

High-Speed 8/4K x 18 Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

5633 tbl 02

Pin Names

Left Port	Right Port	Names		
CEOL, CE1L	\overline{CE} OR, CE1R	Chip Enables ⁽³⁾		
R/WL	R/₩r	Read/Write Enable		
OEL	ŌĒr	Output Enable		
Aol - A12L ⁽¹⁾	Aor - A12r ⁽¹⁾	Address		
I/O0L - I/O17L	1/O0r - 1/017r	Data Input/Output		
CLKL	CLKr	Clock		
ŪBL	ŪBR	Upper Byte Select ⁽²⁾		
LB L	LB R	Lower Byte Select ⁽²⁾		
ADSL	ADS R	Address Strobe		
		Counter Enable		
CNTRST L		Counter Reset		
FT/PIPEL	FT /PIPER	Flow-Through/Pipeline		
V	сс	Power (5V)		
G	ND	Ground (0V)		

NOTES:

- 1. A12 is a NC for IDT709349.
- 2. $\overline{\text{LB}}$ and $\overline{\text{UB}}$ are single buffered regardless of state of $\overline{\text{FT}}/\text{PIPE}$.
- 3. $\overline{CE}o$ and CE1 are single buffered when $\overline{FT}/PIPE = V_{IL}$, $\overline{CE}o$ and CE1 are double buffered when $\overline{FT}/PIPE = V_{IH}$, i.e. the signals take two cycles to deselect.

	tbl	01
--	-----	----

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK		CE1 ⁽⁵⁾	UB ⁽⁴⁾	LB ⁽⁴⁾	R/W	Upper Byte I/O9-17	Lower Byte I/O0-8	Mode
Х	Ŷ	Н	Х	Х	Х	Х	High-Z	High-Z	Deselected—Power Down
Х	Ŷ	Х	L	Х	Х	Х	High-Z	High-Z	Deselected—Power Down
Х	Ŷ	L	Н	Н	Н	Х	High-Z	High-Z	Both Bytes Deselected
Х	Ŷ	L	Н	L	Н	L	DATAIN	High-Z	Write to Upper Byte Only
Х	\uparrow	L	Н	Н	L	L	High-Z	DATAIN	Write to Lower Byte Only
Х	\uparrow	L	Н	L	L	L	DATAIN	DATAIN	Write to Both Bytes
L	\uparrow	L	Н	L	Н	Н	DATAOUT	High-Z	Read Upper Byte Only
L	Ŷ	L	Н	Н	L	Н	High-Z	DATAOUT	Read Lower Byte Only
L	\uparrow	L	Н	L	L	Н	DATAOUT	DATAOUT	Read Both Bytes
Н	Х	L	Н	Х	Х	Х	High-Z	High-Z	Outputs Disabled

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. \overline{ADS} , \overline{CNTEN} , $\overline{CNTRST} = X$.

3. OE is an asynchronous input signa

4. \overline{LB} and \overline{UB} are single buffered regardless of state of \overline{FT} /PIPE.

5. CEo and CE1 are single buffered when FT/PIPE = VIL. CEo and CE1 are double buffered when FT/PIPE = VIH, i.e. the signals take two cycles to deselect.

IDT709359/49L High-Speed 8/4K x 18 Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

5633 tbl 03

5633 tbl 05

Truth Table II—Address Counter Control^(1,2)

External Address	Previous Internal Address	Internal Address Used	CLK	ADS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
An	Х	An	Ŷ	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
х	An	An + 1	Ŷ	Н	L ⁽⁵⁾	Н	D⊮o(n+1)	Counter Enabled—Internal Address generation
Х	An + 1	An + 1	Ŷ	Н	Н	Н	D⊮o(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
Х	Х	A0	Ŷ	Х	Х	L ⁽⁴⁾	Dvo(0)	Counter Reset to Address 0

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. \overline{CE}_{0} , \overline{LB} , \overline{UB} , and \overline{OE} = VIL; CE1 and R/W = VIH.

3. Outputs configured in Flow-Through Output mode: if outputs are in Pipelined mode the data out will be delayed by one cycle.

4. ADS and CNTRST are independent of all other signals including CE0, CE1, UB and LB.

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other signals including CE0, CE1, UB and LB.

Recommended Operating Recommer Temperature and Supply Voltage⁽¹⁾ Recommer

			0
Grade	Ambient Temperature ⁽¹⁾	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%
			5633 tbl 04

NOTES:

 Industrial temperature: for specific speeds, packages and powers contact your sales office.

2. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
Vih	Input High Voltage	2.2		6.0 ⁽¹⁾	V
Vil	Input Low Voltage	-0.5 ⁽²⁾		0.8	V

NOTES:

1. VTERM must not exceed Vcc + 10%.

2. VIL \geq -1.5V for pulse width less than 10ns.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
ЮИТ	DC Output Current	50	mA
			5633 tbl 06

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

 VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

Capacitance⁽¹⁾ (TA = $+25^{\circ}$ C, f = 1.0MHz)

Symbol	Parameter	Conditions ⁽²⁾	Мах.	Unit
Cin	Input Capacitance	VIN = 3dV	9	pF
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF
				5633 tbl 07

NOTES:

 These parameters are determined by device characterization, but are not production tested.

2. 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

3. COUT also references CI/O.

High-Speed 8/4K x 18 Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range (Vcc = 5.0V ± 10%)

			70935		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Lu	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, V_{IN} = 0V to Vcc	_	5	μA
ILO	Output Leakage Current	$\overline{CE}_0 = V_{IH} \text{ or } CE_1 = V_{IL}, V_{OUT} = 0V \text{ to } V_{CC}$	_	5	μA
Vol	Output Low Voltage	lol = +4mA	-	0.4	V
Vон	Output High Voltage	Юн = -4mA	2.4	-	V

NOTE:

1. At $Vcc \le 2.0V$ input leakages are undefined.

5633 tbl 08

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽³⁾ ($Vcc = 5V \pm 10\%$)

						9/49L6 I Only	70935 Com'l			9/49L9 Only	
Symbol	Parameter	Test Condition	Versi	on	Тур. ⁽⁴⁾	Max.	Тур. ⁽⁴⁾	Мах.	Тур. ⁽⁴⁾	Max.	Unit
ICC	Dynamic Operating Current	CEL and CER= VIL	COM'L	L	230	430	210	400	185	360	mA
	(Both Ports Active)	Outputs Disabled f = fMAX ⁽¹⁾	IND	L	_	-	210	440			
ISB1	Standby Current (Both Ports - TTL	$\overline{CEL} = \overline{CER} = VH$	COM'L	L	45	115	40	105	35	95	mA
	Level Inputs)	$f = fMAX^{(1)}$	IND	L		-	40	120			
ISB2		$\label{eq:constraint} \begin{array}{ c c } \hline \overline{C}\overline{E}^*A^* = VIL \mbox{ and } \\ \hline \overline{C}\overline{E}^*B^* = VIH^{(3)} \\ \hline Active \mbox{ Port Outputs} \\ \hline Disabled, \mbox{ f=fMAX}^{(1)} \end{array}$	COM'L	L	150	235	135	220	120	205	mA
	(One Port - TTL Level Inputs)		IND	L		_	135	235		_	
ISB3	Full Standby Current	Both Ports CER and	COM'L	L	0.5	3.0	0.5	3.0	0.5	3.0	mA
	(Both Ports - CMOS Level Inputs)	$ \overline{CEL} \ge VCC - 0.2V VIN \ge VCC - 0.2V or VIN \le 0.2V, f = 0(2) $	IND	L	-		0.5	3.0		-	
ISB4	Full Standby Current	$\overline{CE}^{"A"} \leq 0.2V$ and	COM'L	L	160	210	130	190	110	170	mA
(One Port - CMOS Level Inputs)	$\begin{array}{l} \overline{\text{CE}} \ensuremath{\mathbb{B}}^* & \geq \ensuremath{\mathbb{VC}} & \text{CE} & \text{O}.2 \ensuremath{\mathbb{V}}^{(5)} \\ \overline{\text{VN}} & \geq \ensuremath{\mathbb{VC}} & \text{O}.2 \ensuremath{\mathbb{V}} & \text{O}.2 \mathbb$	IND	L	—		130	205	_			

5633 tbl 09

NOTES:

1. At f = fMax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

- 4. Vcc = 5V, TA = $25^{\circ}C$ for Typ, and are not production tested. Icc Dc(f=0) = 150mA (Typ).
- 5. $CEx = VIL \text{ means } \overline{CE}_{0X} = VIL \text{ and } CE_{1X} = VIH$
 - CEx = VIH means \overline{CE}_{0x} = VIH or CE1x = VIL
 - $CEx \leq 0.2V$ means $\overline{CE} \text{ox} \leq 0.2V$ and $CE1x \geq Vcc$ 0.2V

 $CEx \geq Vcc$ - 0.2V means $\overline{CE}\textsc{ox} \geq Vcc$ - 0.2V or $CE1x \leq 0.2V$

"X" represents "L" for left port or "R" for right port.

IDT709359/49L High-Speed 8/4K x 18 Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

5У

893Ω

5pF*

5633 drw 05

AC Test Conditions

Input Pulse Levels	GND to 3.0V					
Input Rise/Fall Times	2ns Max.					
Input Timing Reference Levels	1.5V					
Output Reference Levels	1.5V					
Output Load	Figures 1, 2 and 3					

5633 tbl 10

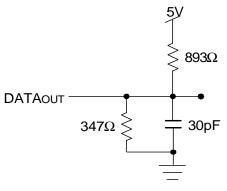




Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tCKLZ, tCKHZ, toLZ, and tOHZ). *Including scope and jig.

 $347\Omega \leq$

DATAOUT

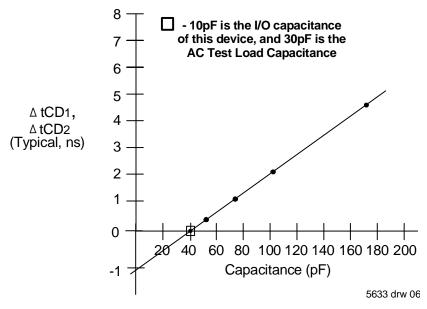


Figure 3. Typical Output Derating (Lumped Capacitive Load).

High-Speed 8/4K x 18 Synchronous Pipelined Dual-Port Static RAM

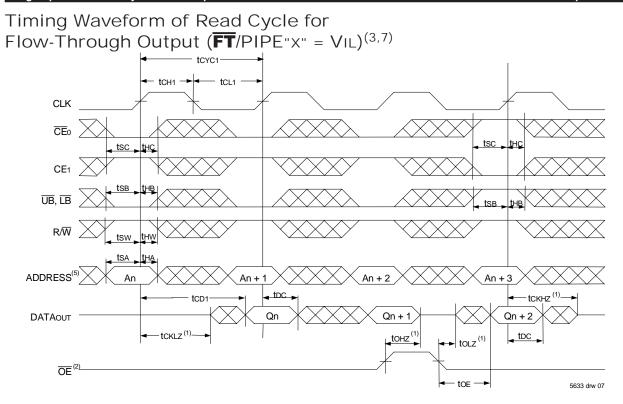
AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)⁽³⁾ ($Vcc = 5V \pm 10\%$, TA = 0°C to +70°C)

			709359/49L6 Com'l Only		709359/49L7 Com'l & Ind		709359/49L9 Com'l Only	
Symbol	Parameter		Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	19		22		25	—	ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	10		12		15		ns
tCH1	Clock High Time (Flow-Through) ⁽²⁾	6.5		7.5		12		ns
tCL1	Clock Low Time (Flow-Through) ⁽²⁾	6.5		7.5		12	—	ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	4		5		6	—	ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	4		5	_	6	—	ns
tR	Clock Rise Time		3		3	—	3	ns
tr	Clock Fall Time		3	_	3	_	3	ns
tsa	Address Setup Time	3.5	_	4	-	4	—	ns
tha	Address Hold Time	0	_	0	_	1	—	ns
tsc	Chip Enable Setup Time	3.5	—	4	_	4	-	ns
tнc	Chip Enable Hold Time	0		0		1	—	ns
tsв	Byte Enable Setup Time	3.5		4	_	4	—	ns
tнв	Byte Enable Hold Time	0		0		1	—	ns
tsw	R/W Setup Time	3.5	_	4	-	4	—	ns
tHW	R/W Hold Time	0	_	0	-	1	—	ns
tsp	Input Data Setup Time	3.5		4	_	4	—	ns
thd	Input Data Hold Time	0	_	0	-	1	_	ns
tsad	ADS Setup Time	3.5	_	4	_	4	_	ns
thad	ADS Hold Time	0	_	0	_	1	—	ns
tscn	CNTEN Setup Time	3.5		4		4	—	ns
then	CNTEN Hold Time	0		0		1		ns
t SRST	CNTRST Setup Time	3.5		4		4		ns
thrst	CNTRST Hold Time	0		0		1		ns
toe	Output Enable to Data Valid		6.5		7.5		9	ns
tolz	Output Enable to Output Low-Z ⁽¹⁾	2		2		2		ns
toнz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽²⁾		15		18		20	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾		6.5		7.5		9	ns
tDC	Data Output Hold After Clock High	2		2		2	—	ns
tскнz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	ns
tскız	Clock High to Output Low-Z ⁽¹⁾	2		2		2		ns
Port-to-Port [Delay	F		•				-
tcwdd	Write Port Clock High to Read Data Delay	—	24		28		35	ns
tccs	Clock-to-Clock Setup Time		9		10		15	ns

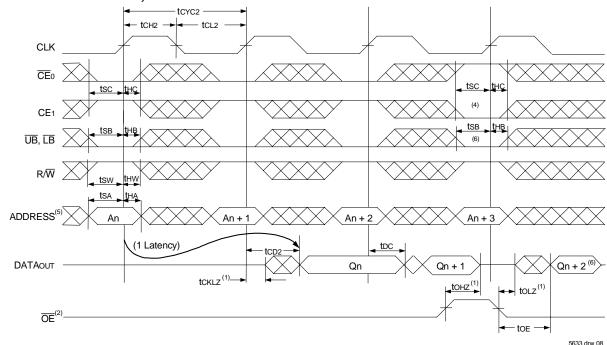
1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

2. The Pipelined output parameters (tcyc2, tcp2) to either the Left or Right ports when FT/PIPE = VIH. Flow-Through parameters (tcyc1, tcp1) apply when FT/PIPE = VIL for that port.

3. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPER and FT/PIPEL.

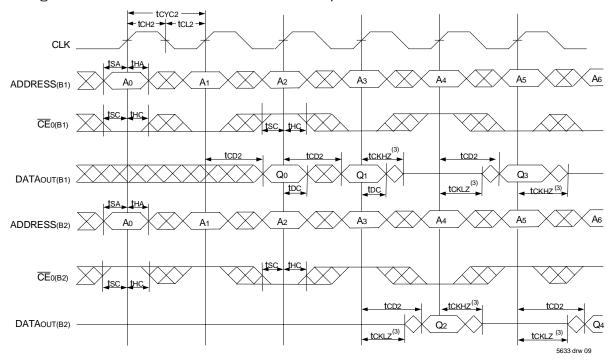


Timing Waveform of Read Cycle for Pipelined Operation $(FT/PIPE"x" = VIH)^{(3,7)}$

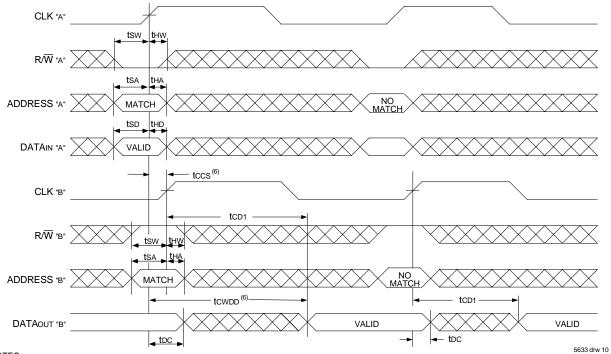


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. \overline{OE} is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = VIL, \overline{CNTEN} \text{ and } \overline{CNTRST} = VIH.$
- 4. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{IH}$, $CE_1 = V_{IL}$, following the next rising edge of the clock. Refer to Truth Table 1.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers
- are for reference use only.
- 6. If UB or LB was HIGH, then the Upper Byte and/or Lower Byte of DATAout for Qn + 2 would be disabled (High-Impedance state).
- 7. "X" here denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read^(1,2)



Timing Waveform of Write with Port-to-Port Flow-Through Read^(4,5,7)

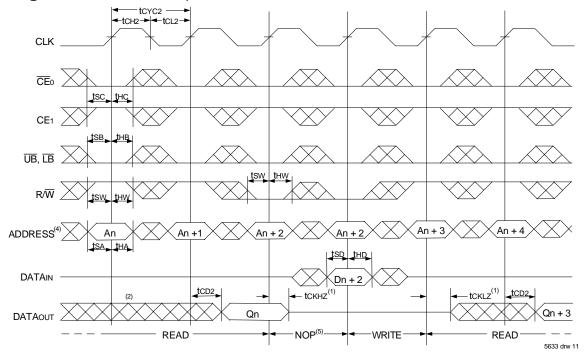


NOTES:

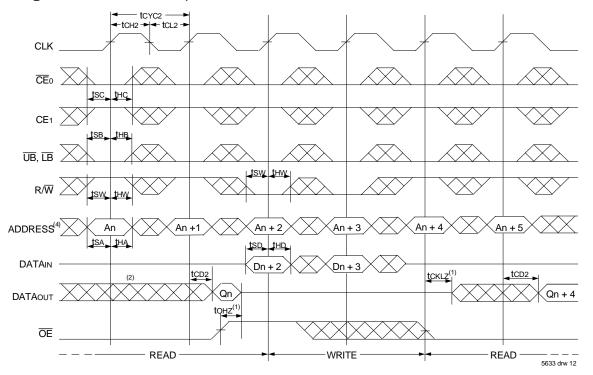
- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT709359/49 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{UB} , \overline{LB} , \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W, \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 3. Transition is measured OmV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $\overline{ADS} = VIL$; CE_1 , \overline{CNTEN} , and $\overline{CNTRST} = VIH$.
- 5. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.
- If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwpp.
 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpp does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

10

Timing Waveform of Pipelined Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽³⁾

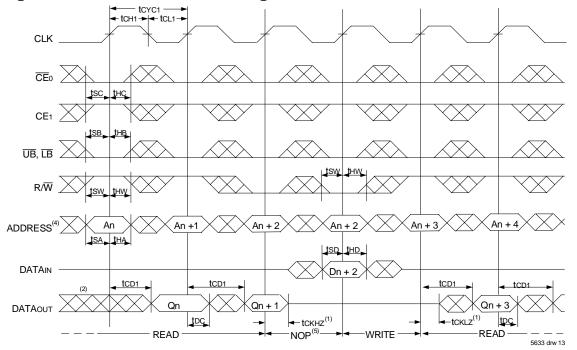


Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽³⁾

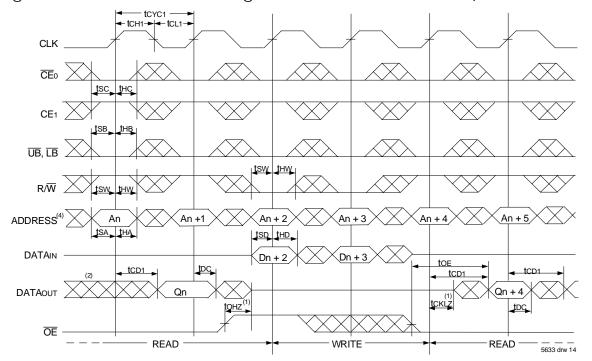


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. CE0, UB, LB, and ADS = VIL; CE1, CNTEN, and CNTRST = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽³⁾

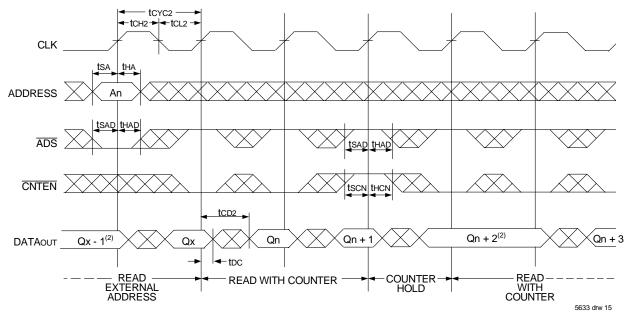


Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽³⁾

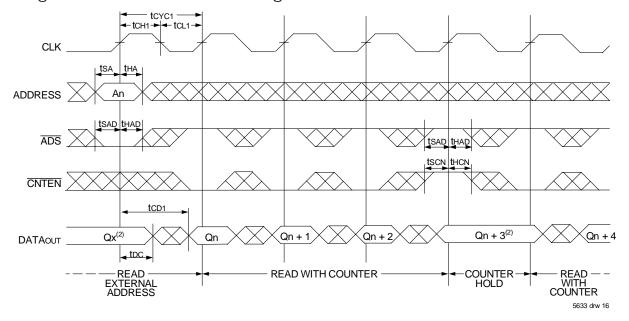


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance is determined by the previous cycle control signals.
- 3. CEo, UB, LB, and ADS = VIL; CE1, CNTEN, and CNTRST = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

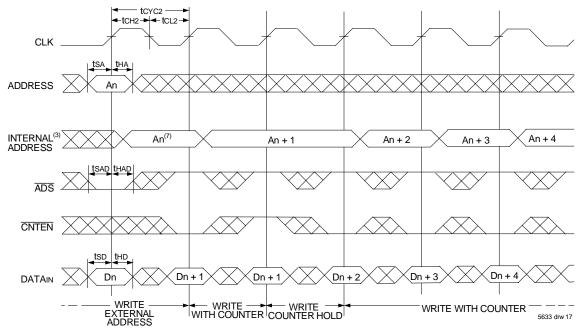


 $Timing \, Waveform \, of \, Flow-Through \, Read \, with \, Address \, Counter \, Advance^{(1)}$

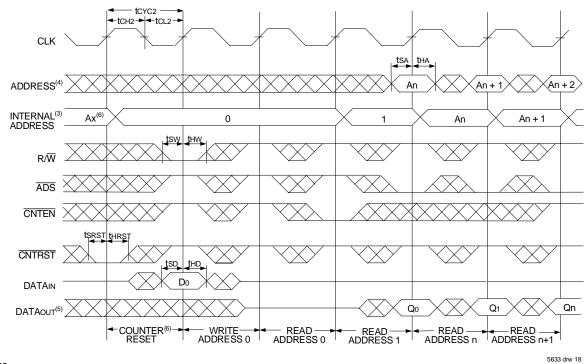


- 1. \overline{CE}_{0} , \overline{OE} , \overline{UB} , and $\overline{LB} = V_{IL}$; CE1, R/W, and $\overline{CNTRST} = V_{IH}$.
- 2. If there is no address change via \overline{ADS} = VIL (loading a new address) or \overline{CNTEN} = VIL (advancing the address), i.e. \overline{ADS} = VIH and \overline{CNTEN} = VIH, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)⁽²⁾



NOTES:

1. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $R/\overline{W} = V_{IL}$; CE_1 and $\overline{CNTRST} = V_{IH}$.

- 3. The "Internal Address" is equal to the "External Address" when $\overline{\text{ADS}}$ = VIL and equals the counter output when $\overline{\text{ADS}}$ = VIH.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
 Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1' Address is written to during this cycle.

^{2.} \overline{CE}_{0} , \overline{UB} , $\overline{LB} = V_{IL}$; $CE_{1} = V_{IH}$.

High-Speed 8/4K x 18 Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

A Functional Description

The IDT709359/49 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

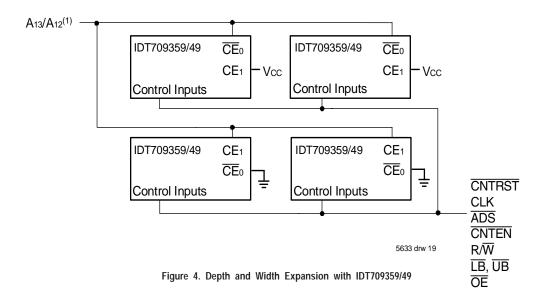
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

 $\overline{CE}_0 = V_{IH}$ or CE1 = VIL for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT709359/49's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{CE}_0 = V_{IL}$ and CE1 = VIH to re-activate the outputs.

Depth and Width Expansion

The IDT709359/49 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT709359/49 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 36-bit or wider applications.

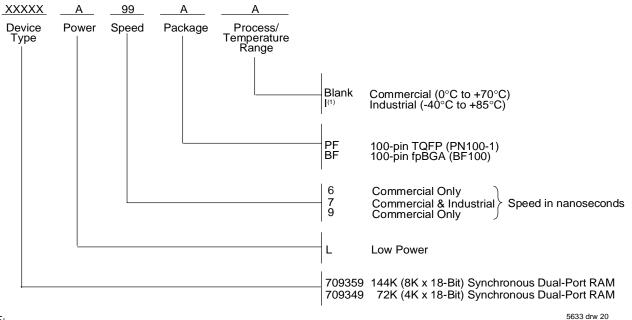




1. A13 is for IDT709359, A12 is for IDT709349.

High-Speed 8/4K x 18 Synchronous Pipelined Dual-Port Static RAM

Ordering Information



NOTE:

1. Contact your local sales office for industrial temp range for other speeds, packages and powers.

IDT Clock Solution for IDT709359/49 Dual-Port

IDT Dual-Port Part Number	Dual-Port I/O Specitications		Clock Specifications				IDT	IDT
	Voltage	I/O	Input Capacitance	Input Duty Cycle Requirement	Maximum Frequency	Jitter Tolerance	PLL Clock Device	Non-PLL Clock Device
709359/49	5	TTL	9pF	40%	100	150ps	FCT88915TT	49FCT805T 49FCT806T 74FCT807T

5633 tbl 12

Datasheet Document History

- 07/08/02: Initial Public Release
- 08/18/03: Removed Preliminary status
 - Page 16 Added IDT Clock Solution Table
- 10/21/08: Page16 Removed "IDT" from orderable part number



CORPORATE HEADQUARTERS 6024 Silver Creek Valley Road San Jose, CA 95138 for SALES: 800-345-7015 or 408-284-8200 fax: 408-284-2775 www.idt.com *for Tech Support:* 408-284-2794 DualPortHelp@idt.com

The IDT logo is a registered trademark of Integrated Device Technology, Inc.